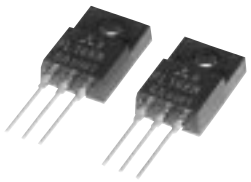
PRELIMINARY
Notice: This is not a final specification.
Some parametric limits are subject to change.

MITSUBISHI Nch POWER MOSFET

FL16KM-6A

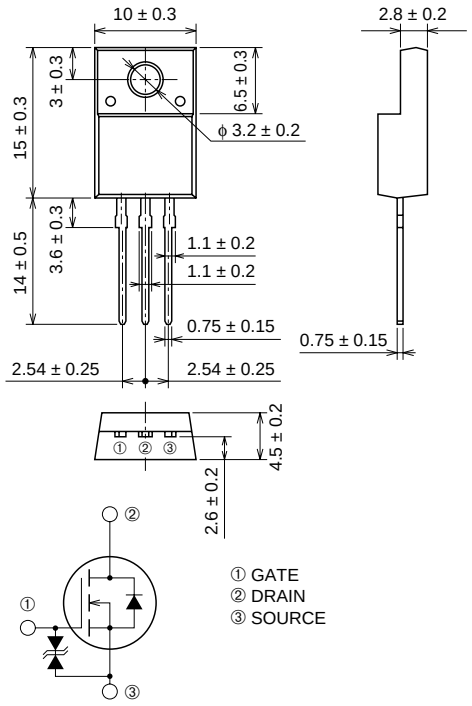
HIGH-SPEED SWITCHING USE

FL16KM-6A



- 10V DRIVE
- V_{DSS} 300V
- $r_{DS\ (ON)\ (MAX)}$ 0.35Ω
- I_D 16A

OUTLINE DRAWING Dimensions in mm



TO-220FN

APPLICATION

Switch mode power supply, Inverter fluorescent lamp, etc.

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	V_{GS} = 0V	300	V
V_{GSS}	Gate-source voltage	V_{DS} = 0V	±30	V
I_D	Drain current		16	A
I_{DM}	Drain current (Pulsed)		48	A
I_{DA}	Avalanche drain current (Pulsed)	L = 200μH	16	A
P_D	Maximum power dissipation		35	W
T_{ch}	Channel temperature		–55 ~ +150	°C
T_{stg}	Storage temperature		–55 ~ +150	°C
V_{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

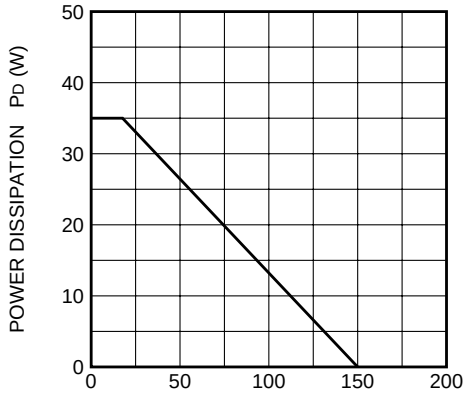
MITSUBISHI ELECTRIC

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

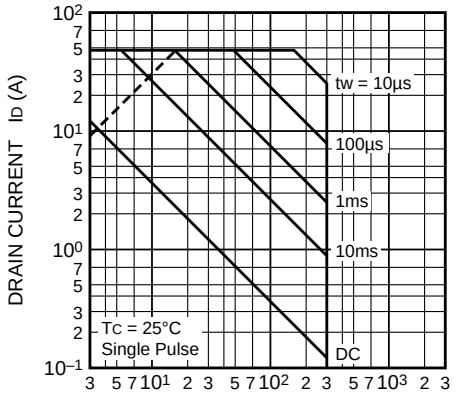
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)\ DSS}$	Drain-source breakdown voltage	I_D = 1mA, V_{GS} = 0V	300	—	—	V
$V_{(BR)\ GSS}$	Gate-source breakdown voltage	I_{GS} = ±100μA, V_{DS} = 0V	±30			V
I_{GSS}	Gate-source leakage current	V_{GS} = ±25V, V_{DS} = 0V	—	—	±10	μA
I_{DSS}	Drain-source leakage current	V_{DS} = 300V, V_{GS} = 0V	—	—	1	mA
$V_{GS\ (th)}$	Gate-source threshold voltage	I_D = 1mA, V_{DS} = 10V	2.0	3.0	4.0	V
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 8A, V_{GS} = 10V	—	0.29	0.35	Ω
$V_{DS\ (ON)}$	Drain-source on-state voltage	I_D = 8A, V_{GS} = 10V	—	2.32	2.80	V
$\lvert y_{fs} \rvert$	Forward transfer admittance	I_D = 8A, V_{DS} = 10V	—	10	—	S
C_{iss}	Input capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	—	950	—	pF
C_{oss}	Output capacitance		—	175	—	pF
C_{rss}	Reverse transfer capacitance		—	20	—	pF
$t_{d\ (on)}$	Turn-on delay time	V_{DD} = 150V, I_D = 8A, V_{GS} = 10V, R_{GEN} = R_{GS} = 50Ω	—	15	—	ns
t_r	Rise time		—	30	—	ns
$t_{d\ (off)}$	Turn-off delay time		—	150	—	ns
t_f	Fall time		—	60	—	ns
V_{SD}	Source-drain voltage	I_S = 8A, V_{GS} = 0V	—	1.5	2.0	V
$R_{th\ (ch-c)}$	Thermal resistance	Channel to case	—	—	3.57	°C/W

PERFORMANCE CURVES

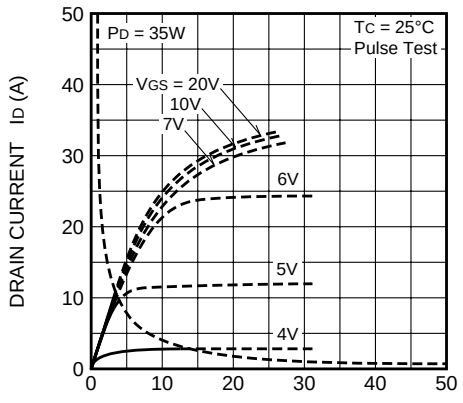
POWER DISSIPATION DERATING CURVE



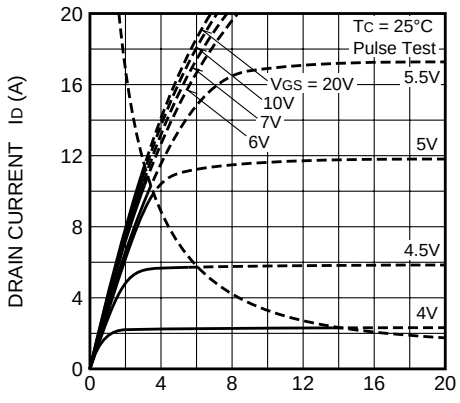
MAXIMUM SAFE OPERATING AREA



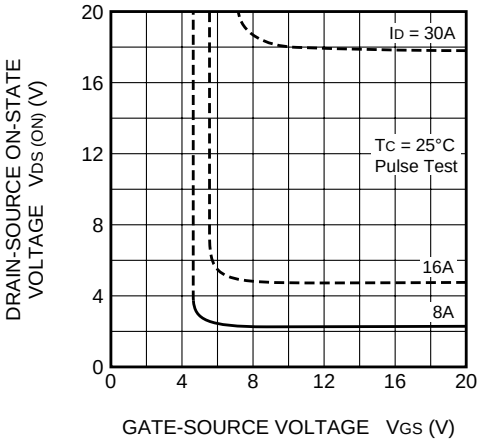
OUTPUT CHARACTERISTICS (TYPICAL)



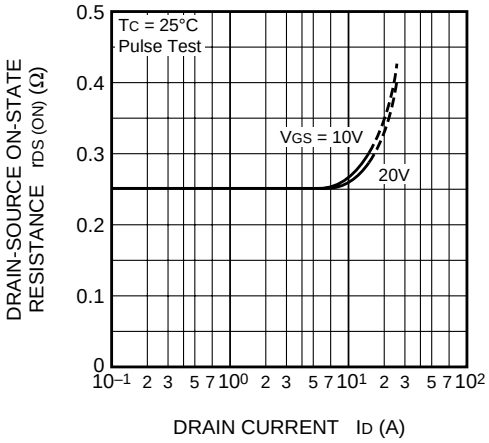
OUTPUT CHARACTERISTICS (TYPICAL)



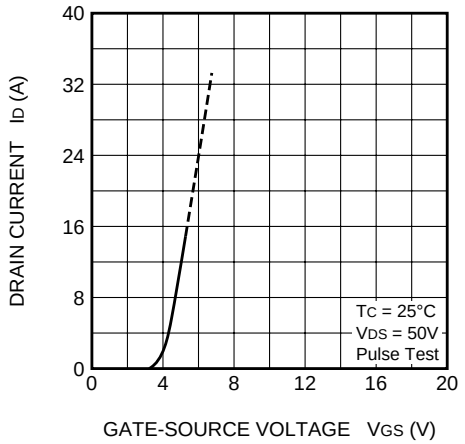
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



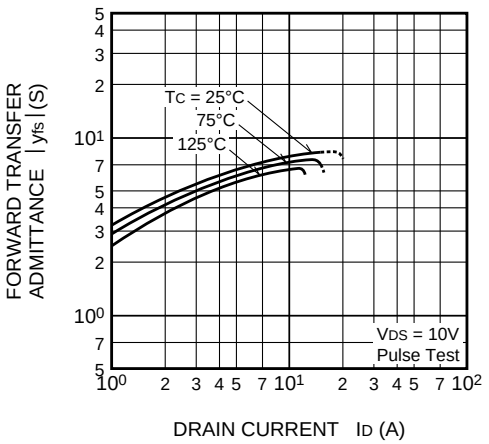
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



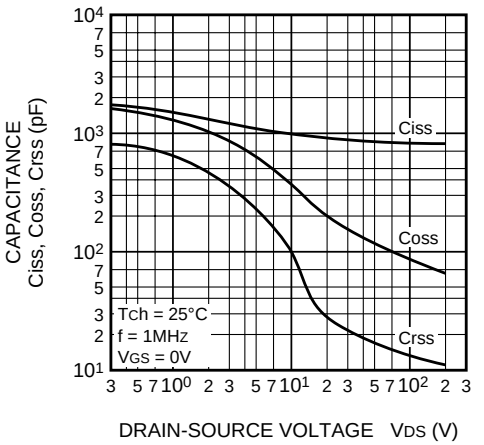
TRANSFER CHARACTERISTICS (TYPICAL)



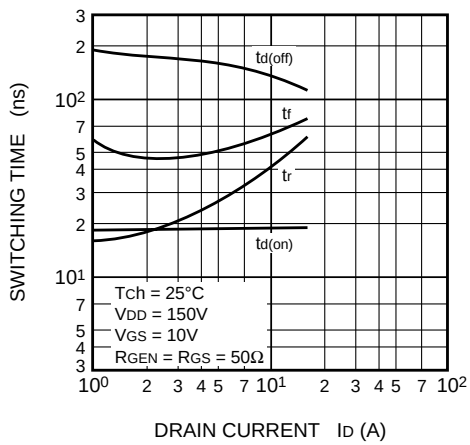
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



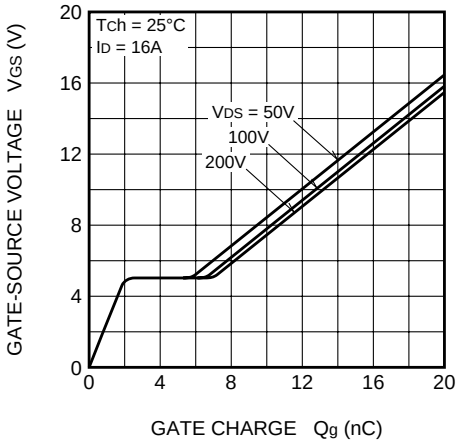
CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



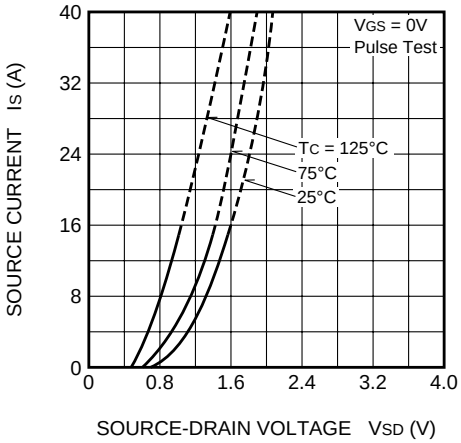
SWITCHING CHARACTERISTICS (TYPICAL)



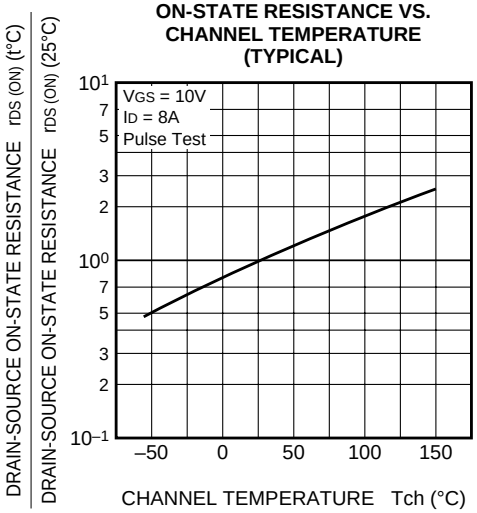
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



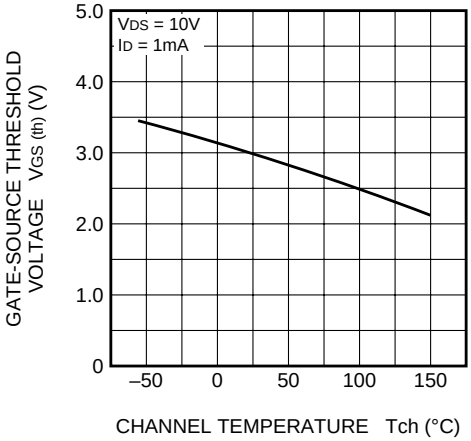
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



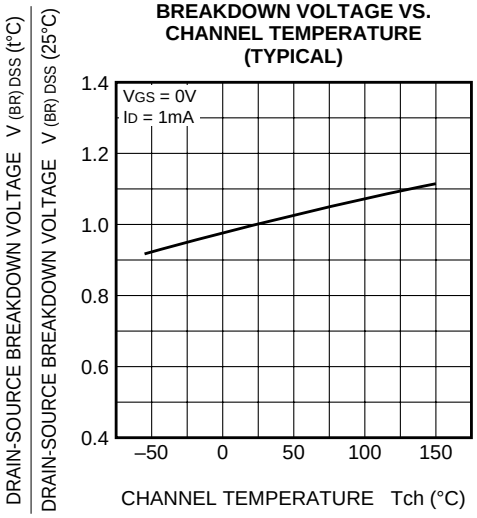
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS